

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
	G05092A		1 of 1

TYPE : 6PT2810N3T**

CHIP SIZE	1.40 * 1.40 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	7,538 pcs

Maximum Ratings (Ta=25°C)

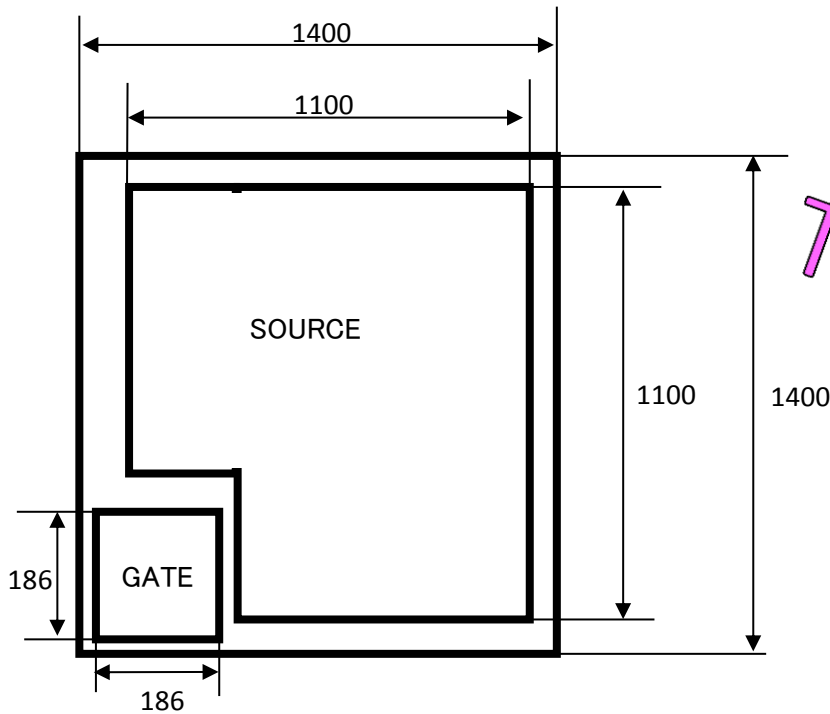
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	100	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	2	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT			CONDITIONS
		MIN.	MAX.	UNIT	
1	IGSS		±15	uA	VGS= ±20V VDS= 0V
2	IDSS		100	nA	VDS= 100V
3	BVDSS	110		V	ID= 10uA
4	Vth	1.5	2.5	V	ID= 250uA
5	RDS(on) 1		0.3	Ω	ID= 2.0A VGS= 10V
6	RDS(on) 2		0.35	Ω	ID= 1.0A VGS= 4.5V
7	VSD	0.5	1.1	V	IS= 1A VGS= 0V
8	Yfs	500		mS	VDS= 10V ID= 200mA

※ Built-in ZD between Gate and Source



NOTE: